

	Application No.	Applicant(s)	
Notice of Allowability	10/676,983	LI ET AL.	
	Examiner	Art Unit	
	Lan Vinh	1765	
- The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT F of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED I) or other appropriate comm RIGHTS. This application is 3 and MPEP 1308.	in this application. If not included nunication will be mailed in due course. THI S	
1. This communication is responsive to <u>Amendment filed on</u>	<u>12/13/2005</u> .		
2. The allowed claim(s) is/are <u>1-4,7-12,14-16 and 18</u> .			
 3. Acknowledgment is made of a claim for foreign priority unally All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents 	e been received. e been received in Applicat	on No	<u>.</u>
International Bureau (PCT Rule 17.2(a)).		od in the national stage application from the	•
* Certified copies not received:			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDON! THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the requirements	
4. A SUBSTITUTE OATH OR DECLARATION must be submiNFORMAL PATENT APPLICATION (PTO-152) which give			
5. CORRECTED DRAWINGS (as "replacement sheets") mu	st be submitted.		
(a) I including changes required by the Notice of Draftsper	son's Patent Drawing Revie	w (PTO-948) attached	
1) hereto or 2) to Paper No./Mail Date	<u>.</u> .		
(b) including changes required by the attached Examiner Paper No./Mail Date			
Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in	1.84(c)) should be written on the header according to 37 C	the drawings in the front (not the back) of FR 1.121(d).	
 DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT 			
Address and A.V.			
Attachment(s) 1. ☐ Notice of References Cited (PTO-892)	5 ☐ Notice of I	nformal Patent Application (PTO-152)	
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)		Summary (PTO-413),	
3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/	Paper No 'Paper No '7. ☐ Examiner'	./Mail Date s Amendment/Comment	
Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit		s Statement of Reasons for Allowance	
of Biological Material	9.		
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		Lan Vinh AU 1765	

U.S. Patent and Trademark Office PTOL-37 (Rev. 7-05) Application/Control Number: 10/676,983

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DETAILED ACTION

Allowable Subject Matter

1. Claims 1-4, 7-12, 14-16, 18 allowed

The following is an examiner's statement of reasons for allowance:

Regarding claim 1, the cited prior art of record fails to disclose or suggest a method for selective etching a metal oxide layer comprises the step of patterning and selectively etching the metal thin film without substantially over etching into an adjacent oxide layer, including etching the metal thin film using BCI and CI gas in an etching chamber, wherein the etching chamber pressure is maintained at a pressure of about 6 mTorr, and wherein BCI is delivered at a flow rate of about 30 sccm and CI is delivered at a flow rate of about 60 sccm, in combination with the rest of the steps/limitations of claim 1. Regarding claim 9, the cited prior art of record fails to disclose or suggest a method for selective etching a metal oxide layer comprises the step of selectively etching the metal thin film without substantially over etching into an adjacent oxide layer including etching the metal thin film using BCI and C1 gas in an etching chamber, including providing a Tcp RF of about 350 W at a Bias RF of about 150 W at a pressure of about 6 torr, in combination with the rest of the steps/limitations of claim 9. Regarding claim 15, the cited prior art of record fails to disclose or suggest a method for selective etching a metal oxide layer comprises the step of selectively etching the metal thin film without substantially over etching into an adjacent oxide layer includes etching the exposed metal thin film with etching chemicals consisting of BCI, delivered at a flow-rate of between about 10 sccm to 60 sccm, and CI with a flow rate of between about 20

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sccm to I 0.0 sccm, wherein the volume of CI is twice that of BC1, and generating a Tcp RF plasma of about 350 W and a Bias RF plasma of about 150 W. while maintaining the backward plasma less than I %, in combination with the rest of the steps/limitations of claim 15.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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February 1, 2006